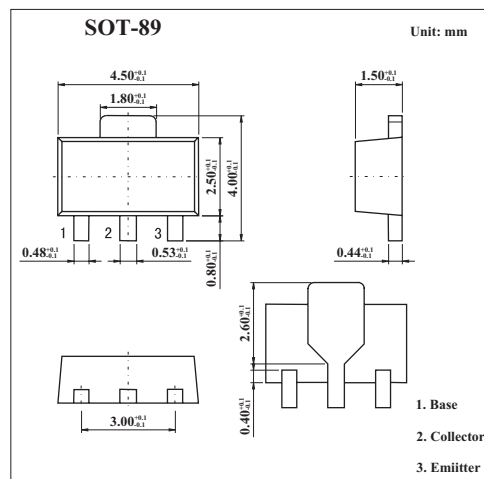


Low Frequency Transistor

2SC4672

■ Features

- Low Saturation Voltage, Typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$
- Excellent DC Current Gain Characteristics
- Complements the 2SA1797

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	60	V
Collector-Emitter Voltage	V_{CE0}	50	V
Emitter-Base Voltage	V_{EB0}	6	V
Collector Current	I_C	3	A (DC)
		6	A (Pulse) *1
Collector Power Dissipation	P_C	0.5	W
		2 *2	
Junction temperature	T_j	150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

*1 Single Pulse, $P_w = 10ms$

*2 40 x 40 x 1.0mm Ceramic board

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60V$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V$			0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu A$	60			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA$	50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu A$	6			V
DC Current Transfer Ratio	h_{FE}	$V_{CE} = 2V, I_C = 0.5A$ *	82		270	
		$V_{CE} = 2V, I_C = 1.5A$ *	45			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 50mA$ *		0.13	0.35	V
Transistion frequency	f_T	$V_{CE} = 2V, I_E = -0.5A, f = 100MHz$		210		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		25		pF

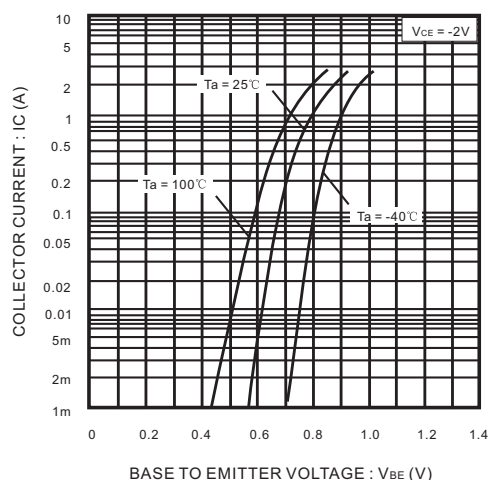
* Measured using pulse current.

2SC4672

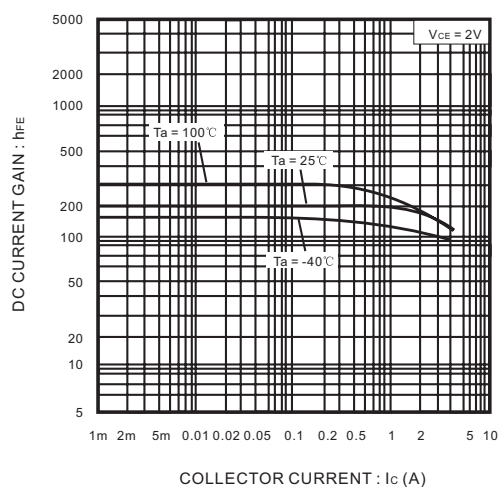
■ hFE Classification

Marking	DK	
Rank	P	Q
hFE	82 ~ 180	120 ~ 270

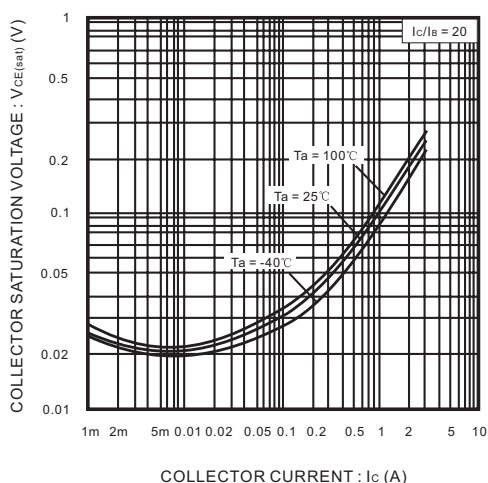
■ Electrical Characteristics Curves



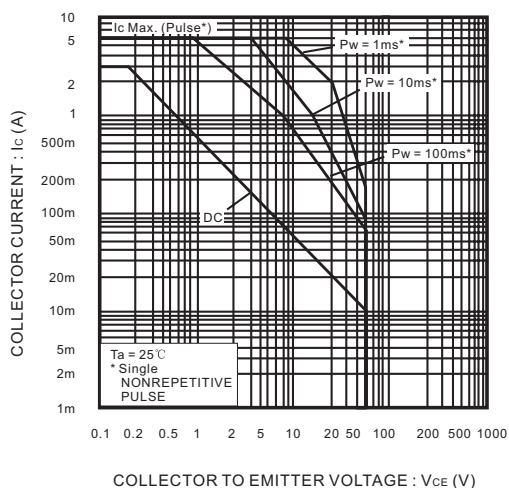
Grounded emitter propagation characteristics



DC current gain vs. Collector current



Collector-emitter saturation voltage vs. Collector current



Safe Operating area